

GaAs-IR-Lumineszenzdiode

GaAs Infrared Emitter

LD 274



Wesentliche Merkmale

- GaAs-LED mit sehr hohem Wirkungsgrad
- Hohe Zuverlässigkeit
- Gute spektrale Anpassung an Si-Fotoempfänger
- Gehäusegleich mit SFH 484

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Sensorik
- Diskrete Lichtschranken

Features

- Very highly efficient GaAs-LED
- High reliability
- Spectral match with silicon photodetectors
- Same package as SFH 484

Applications

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Sensor technology
- Discrete interrupters

| Typ Type | Bestellnummer Ordering Code | Gehäuse Package |
|-------------|--------------------------------|---|
| LD 274 | Q62703-Q1031 | 5-mm-LED-Gehäuse ($T\ 1\ \frac{3}{4}$), graugetöntes Epoxy-Gießharz, Anschlüsse im 2.54-mm-Raster ($\frac{1}{10}$ "), Kathodenkennzeichnung: Kürzerer Lötspieß, flat |
| LD 274-3 | Q62703-Q1820 | 5 mm LED package ($T\ 1\ \frac{3}{4}$), grey colored epoxy resin lens, solder tabs lead spacing 2.54 mm ($\frac{1}{10}$ "), cathode marking: shorter solder lead, flat |

Grenzwerte ($T_A = 25^\circ\text{C}$)**Maximum Ratings**

| Bezeichnung Parameter | Symbol Symbol | Wert Value | Einheit Unit |
|--|---------------------------------|-----------------------|-------------------------|
| Betriebs- und Lagertemperatur Operating and storage temperature range | $T_{\text{op}}; T_{\text{stg}}$ | - 40 ... + 100 | °C |
| Sperrspannung Reverse voltage | V_R | 5 | V |
| Durchlaßstrom Forward current | I_F | 100 | mA |
| Stoßstrom, $t_p = 10 \mu\text{s}, D = 0$ Surge current | I_{FSM} | 3 | A |
| Verlustleistung Power dissipation | P_{tot} | 165 | mW |
| Wärmewiderstand Thermal resistance | R_{thJA} | 450 | K/W |

Kennwerte ($T_A = 25^\circ\text{C}$)**Characteristics**

| Bezeichnung Parameter | Symbol Symbol | Wert Value | Einheit Unit |
|---|------------------------------|-----------------------|-------------------------|
| Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | λ_{peak} | 950 | nm |
| Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | $\Delta\lambda$ | 55 | nm |
| Abstrahlwinkel Half angle | ϕ | ± 10 | Grad |
| Aktive Chipfläche Active chip area | A | 0.09 | mm ² |
| Abmessungen der aktiven Chipfläche Dimension of the active chip area | $L \times B$ $L \times W$ | 0.3×0.3 | mm |
| Abstand Chipoberfläche bis Linsenscheitel Distance chip front to lens top | H | 4.9 ... 5.5 | mm |
| Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100 \text{ mA}, R_L = 50 \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100 \text{ mA}, R_L = 50 \Omega$ | t_r, t_f | 0.5 | μs |

Kennwerte ($T_A = 25^\circ\text{C}$)

Characteristics (cont'd)

| Bezeichnung Parameter | Symbol Symbol | Wert Value | Einheit Unit |
|---|------------------|--|-----------------|
| Kapazität Capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$ | C_o | 25 | pF |
| Durchlaßspannung Forward voltage $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ $I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$ | V_F V_F | 1.30 (≤ 1.5) 1.90 (≤ 2.5) | V V |
| Sperrstrom, $V_R = 5 \text{ V}$ Reverse current | I_R | 0.01 (≤ 1) | μA |
| Gesamtstrahlungsfluß Total radiant flux $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | Φ_e | 15 | mW |
| Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100 \text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100 \text{ mA}$ | TC_I | - 0.55 | %/K |
| Temperaturkoeffizient von V_F , $I_F = 100 \text{ mA}$ Temperature coefficient of V_F , $I_F = 100 \text{ mA}$ | TC_V | - 1.5 | mV/K |
| Temperaturkoeffizient von λ , $I_F = 100 \text{ mA}$ Temperature coefficient of λ , $I_F = 100 \text{ mA}$ | TC_λ | + 0.3 | nm/K |

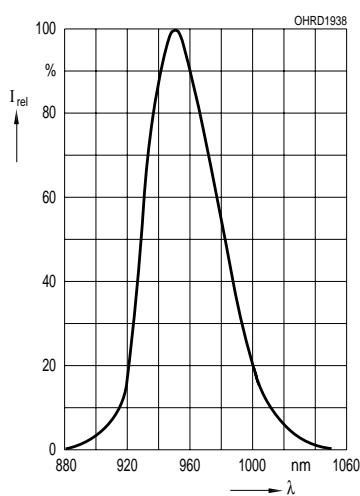
Gruppierung der Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.001 \text{ sr}$ **Grouping of Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.001 \text{ sr}$

| Bezeichnung Parameter | Symbol Symbol | Wert Value | | | Einheit Unit |
|--|--|-----------------------|------------------------------|-----------------|-------------------------|
| | | LD 274 | LD 274-2¹⁾ | LD 274-3 | |
| Strahlstärke Radiant intensity $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | $I_e \text{ min}$ $I_e \text{ max}$ | 50 — | 50 100 | 80 — | mW/sr mW/sr |
| Strahlstärke Radiant intensity $I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$ | $I_e \text{ typ.}$ | 350 | 600 | 800 | mW/sr |

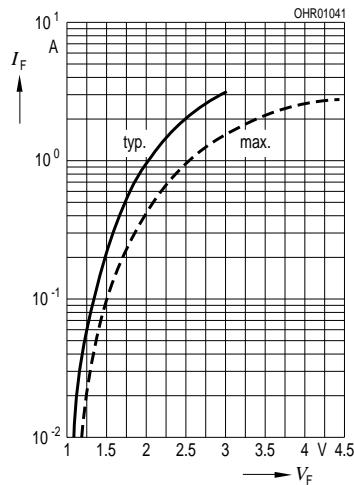
¹⁾ Nur auf Anfrage lieferbar.¹⁾ Available only on request.

Relative Spectral Emission

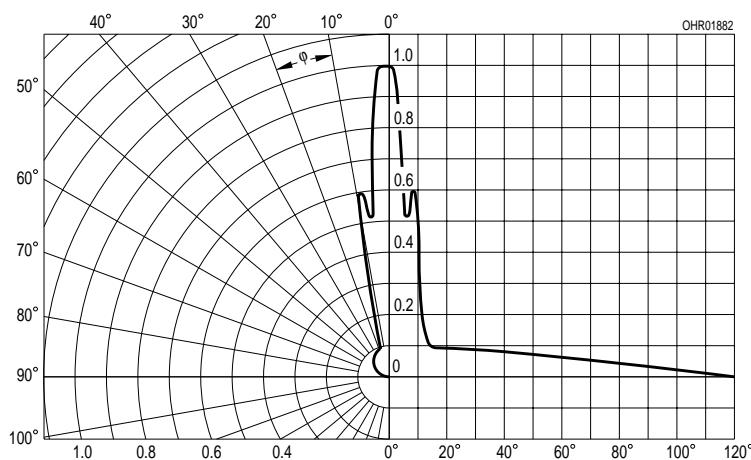
$$I_{\text{rel}} = f(\lambda)$$

**Forward Current**

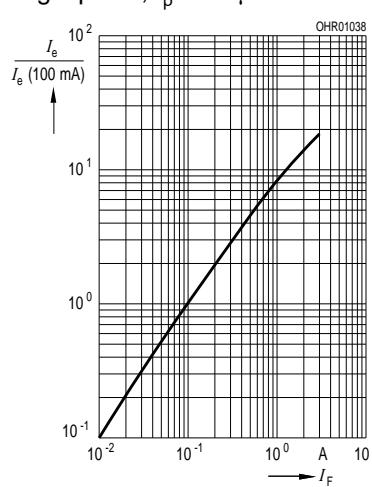
$$I_F = f(V_F), \text{ single pulse, } t_p = 20 \mu\text{s}$$

**Radiation Characteristics,**

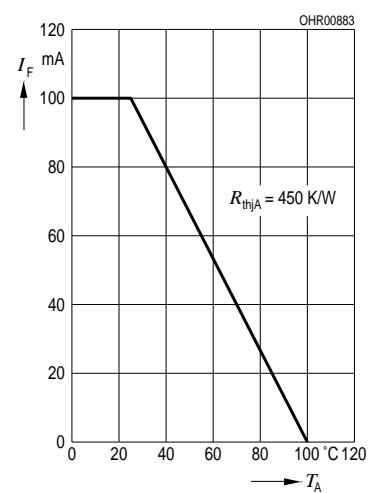
$$I_{\text{rel}} = f(\phi)$$

**Radiant Intensity $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$**

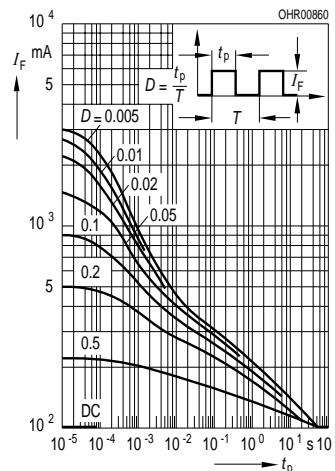
Single pulse, $t_p = 20 \mu\text{s}$

**Max. Permissible Forward Current**

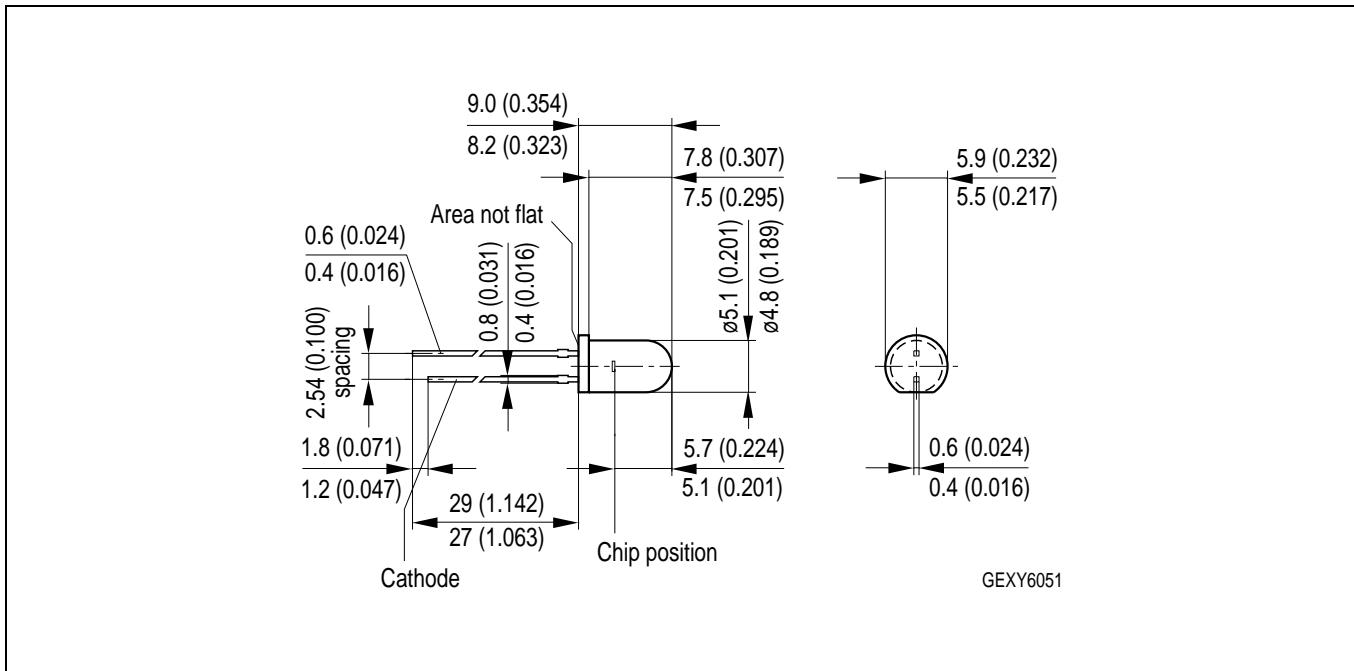
$$I_F = f(T_A)$$

**Permissible Pulse Handling**

$$\text{Capability } I_F = f(\tau), T_C \leq 25 \text{ }^{\circ}\text{C}, \text{ duty cycle } D = \text{ parameter}$$



Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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